

FQB6N45 / FQI6N45

450V N-Channel MOSFET

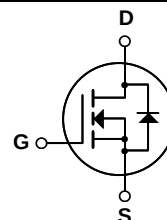
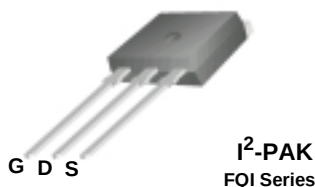
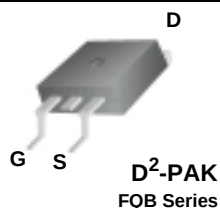
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, electronic lamp ballast based on half bridge.

Features

- 6.2A, 450V, $R_{DS(on)} = 1.1\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 16 nC)
- Low C_{rss} (typical 11 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB6N45 / FQI6N45	Units
V_{DSS}	Drain-Source Voltage	450	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	6.2	A
	- Continuous ($T_C = 100^\circ\text{C}$)	3.9	A
I_{DM}	Drain Current - Pulsed (Note 1)	25	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	350	mJ
I_{AR}	Avalanche Current (Note 1)	6.2	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	9.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	98	W
	- Derate above 25°C	0.78	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.28	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	450	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.47	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 450\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 360\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.1\text{ A}$	--	0.86	1.1	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 3.1\text{ A}$ (Note 4)	--	4.6	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	620	810	pF
C_{oss}	Output Capacitance		--	95	125	pF
C_{rss}	Reverse Transfer Capacitance		--	11	15	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 225\text{ V}, I_D = 6.2\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	15	40	ns
t_r	Turn-On Rise Time		--	70	150	ns
$t_{d(off)}$	Turn-Off Delay Time		--	30	70	ns
t_f	Turn-Off Fall Time		--	40	90	ns
Q_g	Total Gate Charge	$V_{DS} = 360\text{ V}, I_D = 6.2\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	16	21	nC
Q_{gs}	Gate-Source Charge		--	4.3	--	nC
Q_{gd}	Gate-Drain Charge		--	7.8	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	6.2	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	25	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 6.2 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 6.2 A, dI _F / dt = 100 A/μs (Note 4)	--	210	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.4	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 16\text{ mH}, I_{AS} = 6.2\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 6.2\text{ A}, dI/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

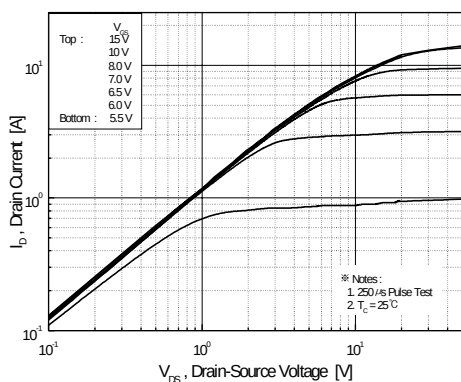


Figure 1. On-Region Characteristics

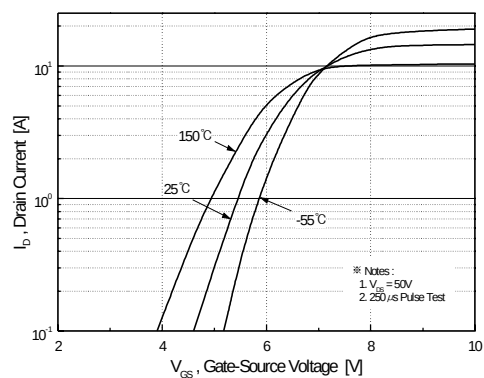


Figure 2. Transfer Characteristics

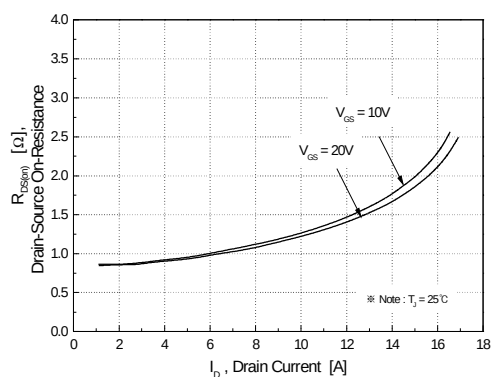


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

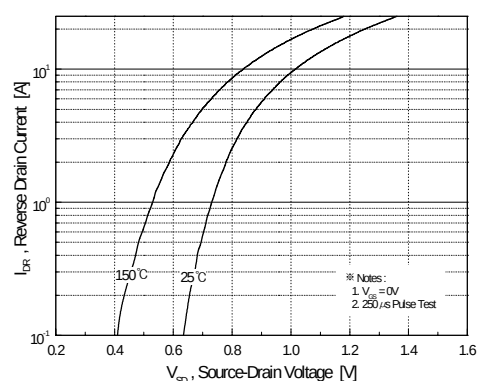


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

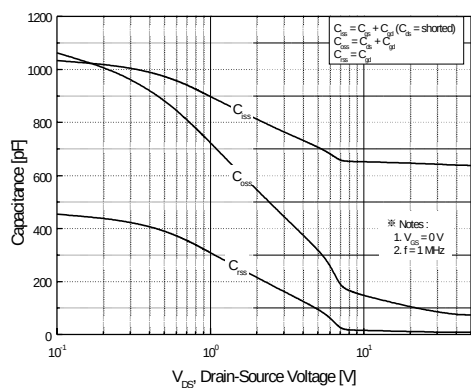


Figure 5. Capacitance Characteristics

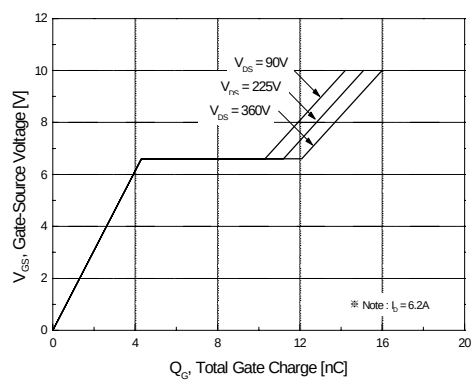


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

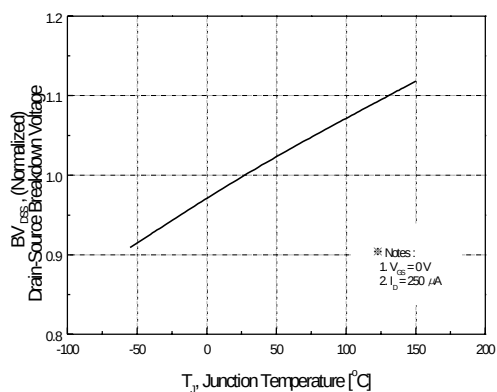


Figure 7. Breakdown Voltage Variation vs. Temperature

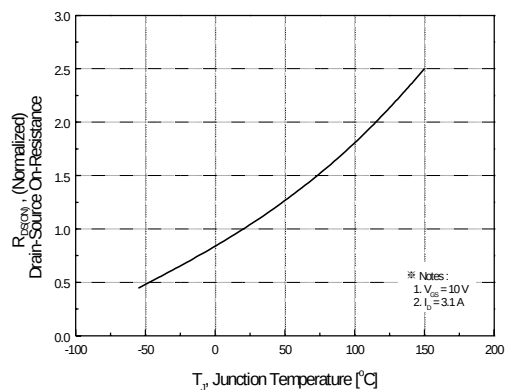


Figure 8. On-Resistance Variation vs. Temperature

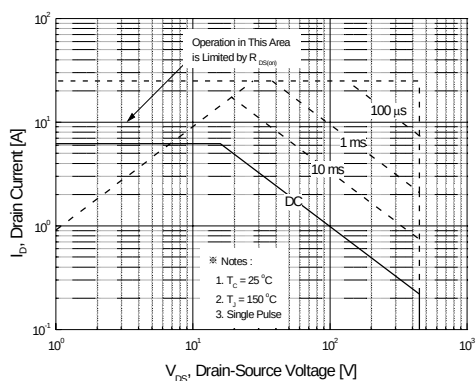


Figure 9. Maximum Safe Operating Area

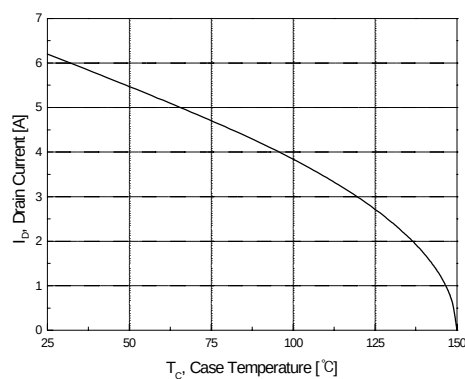


Figure 10. Maximum Drain Current vs. Case Temperature

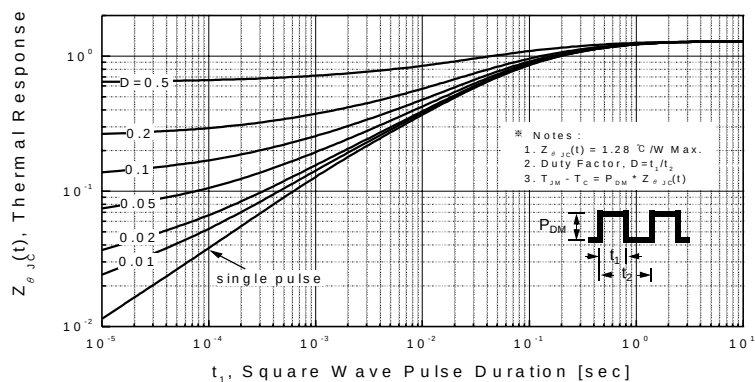
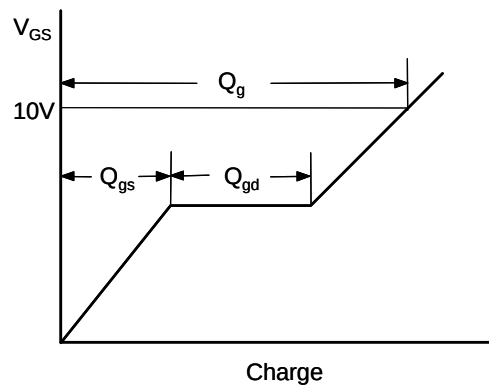
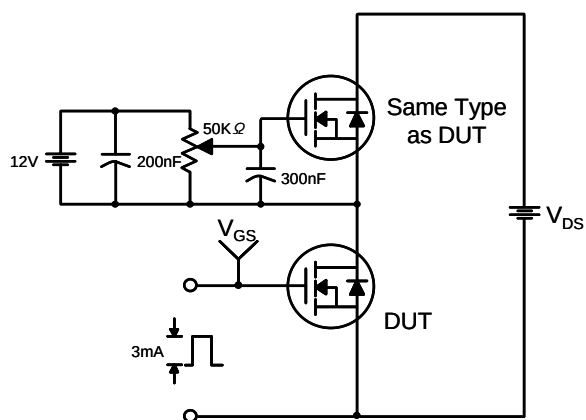
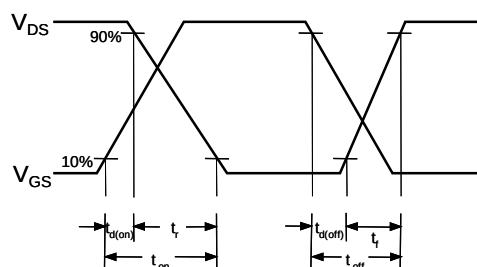
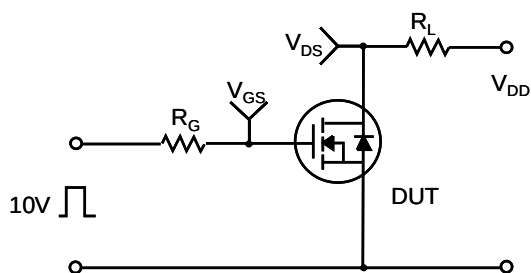


Figure 11. Transient Thermal Response Curve

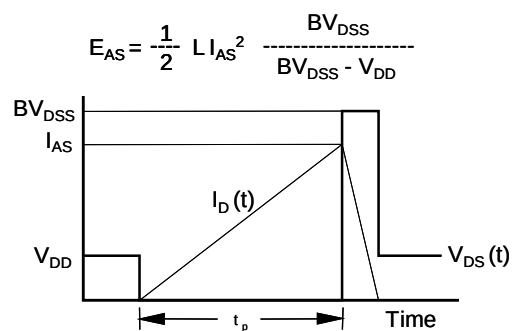
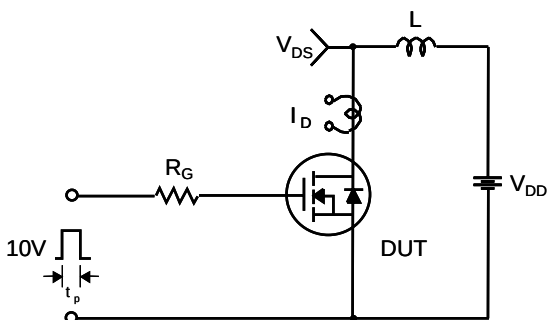
Gate Charge Test Circuit & Waveform

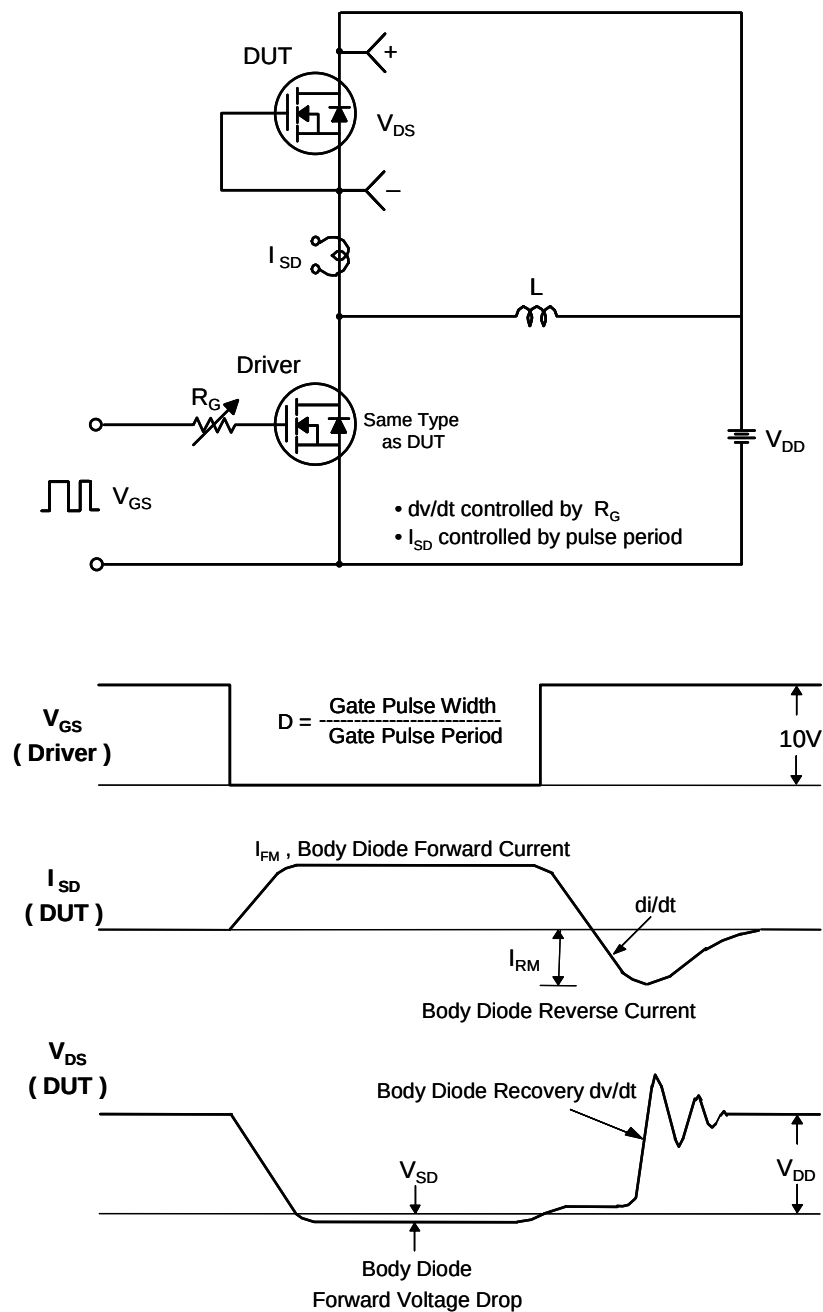


Resistive Switching Test Circuit & Waveforms



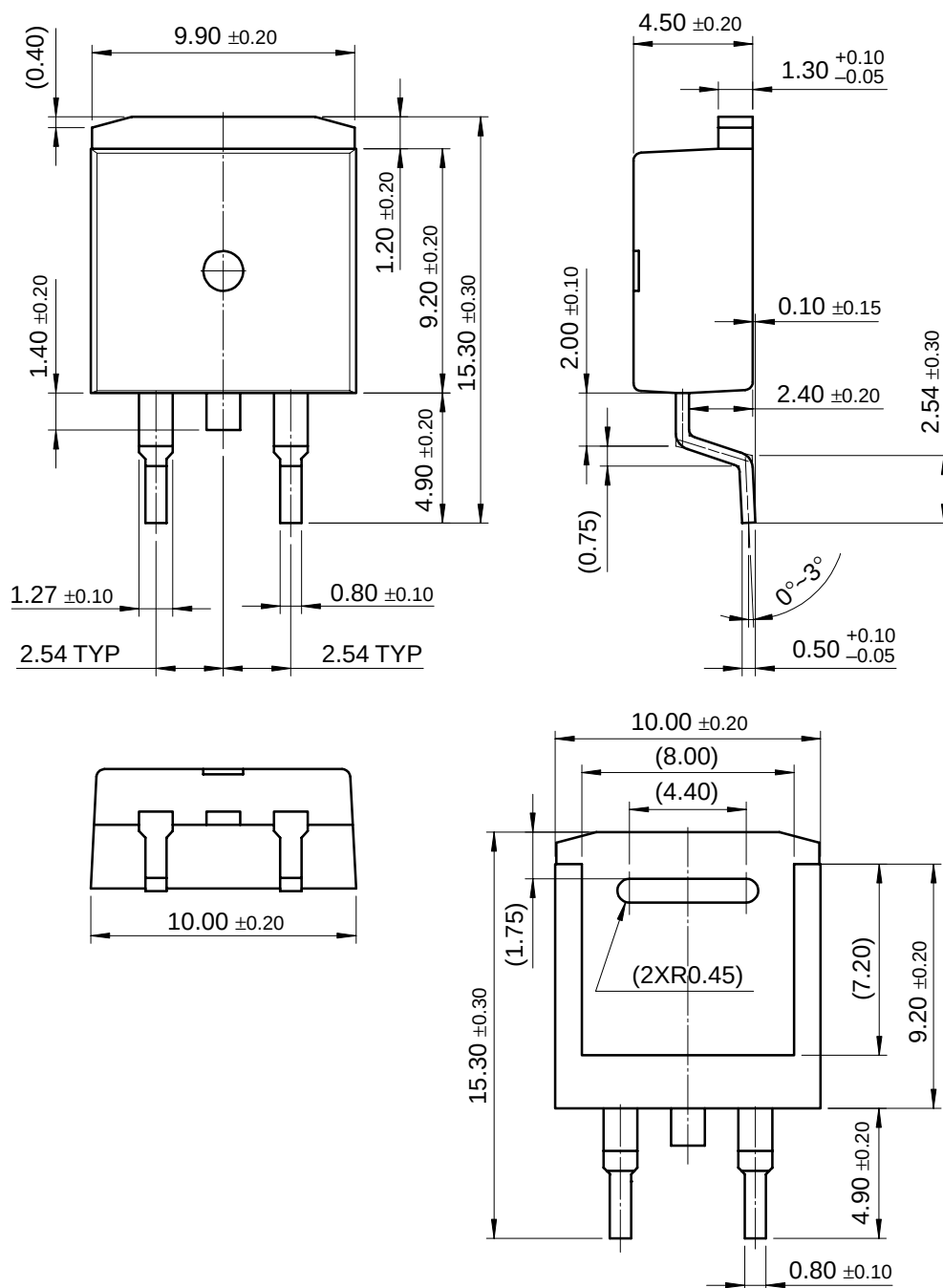
Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

Package Dimensions

D²PAK



FQIB6N45 / FQI6N45

Technical drawing of a 3-pin connector, showing three views: front, side, and top.

Front View Dimensions:

- Overall Width: 9.90 ± 0.20
- Overall Height: 13.08 ± 0.20
- Top Flange Height: (0.40)
- Pin 1 (Left) Width: 1.27 ± 0.10
- Pin 2 (Middle) Width: 1.47 ± 0.10
- Pin 3 (Right) Width: 0.80 ± 0.10
- Pin 2 Chamfer: 45°
- Pin 2 Length: 1.20 ± 0.20
- Pin 2 Spacing: 9.20 ± 0.20
- Pin 2 Max Length: $\text{MAX } 13.40$
- Pin 2 Max Width: $\text{MAX } 3.00$
- Pin 2 Total Height: 10.08 ± 0.20
- Pin 2 Spacing (Typical): 2.54 TYP

Side View Dimensions:

- Overall Height: 4.50 ± 0.20
- Pin 2 Width: $1.30^{+0.10}_{-0.05}$
- Pin 2 Height: $0.50^{+0.10}_{-0.05}$
- Pin 2 Spacing: 2.40 ± 0.20

Top View Dimensions:

- Overall Width: 10.00 ± 0.20

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FASTr™	QFET™	VCX™
Bottomless™	GlobalOptoisolator™	QS™	
CoolFET™	GTO™	QT Optoelectronics™	
CROSSVOLT™	HiSeC™	Quiet Series™	
DOME™	ISOPLANAR™	SuperSOT™-3	
E ² CMOS™	MICROWIRE™	SuperSOT™-6	
EnSigna™	OPTOLOGIC™	SuperSOT™-8	
FACT™	OPTOPLANAR™	SyncFET™	
FACT Quiet Series™	POP™	TinyLogic™	
FAST®	PowerTrench®	UHC™	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



О компании

ООО "ТрейдЭлектроникс" - это оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов. Реализуемая нашей компанией продукция насчитывает более полумиллиона наименований.

Благодаря этому наша компания предлагает к поставке практически не ограниченный ассортимент компонентов как оптовыми, мелкооптовыми партиями, так и в розницу.

Наличие собственной эффективной системы логистики обеспечивает надежную поставку продукции по конкурентным ценам в точно указанные сроки.

Срок поставки со стоков в **Европе и Америке – от 3 до 14 дней.**

Срок поставки из **Азии – от 10 дней.**

Благодаря развитой сети поставщиков, помогаем в поиске и приобретении экзотичных или снятых с производства компонентов.

Предоставляем спец цены на элементы для создания инженерных сэмплов.

Упорный труд, качественный результат дают нам право быть уверенными в себе и надежными для наших клиентов.

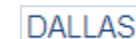
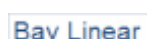
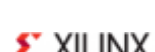
Наша компания это:

- Гарантия качества поставляемой продукции
- Широкий ассортимент
- Минимальные сроки поставок
- Техническая поддержка
- Подбор комплектации
- Индивидуальный подход
- Гибкое ценообразование

Наша организация особенно сильна в поставках модулей, микросхем, пассивных компонентов, ксайленсах (XC), EPF, EPM и силовой электроники.

Большой выбор предлагаемой продукции, различные виды оплаты и доставки, позволят Вам сэкономить время и получить максимум выгоды от сотрудничества с нами!

Перечень производителей, продукцию которых мы поставляем на российский рынок





Trade Electronics.ru

гарантия бесперебойности производства и
качества выпускаемой продукции

С удовольствием будем прорабатывать для Вас поставки всех необходимых компонентов по текущим запросам для скорейшего выявления групп элементов, по которым сотрудничество именно с нашей компанией будет для Вас максимально выгодным!

С уважением,

Менеджер отдела продаж ООО

«Трейд Электроникс»

Шишлаков Евгений

8 (495)668-30-28 доб 169

manager28@tradeelectronics.ru

<http://www.tradeelectronics.ru/>